

## P-Channel 30-V (D-S) MOSFET

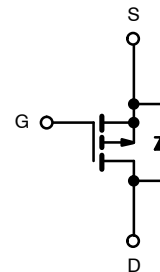
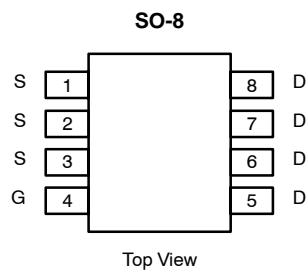
PRODUCT SUMMARY		
$V_{DS}$ (V)	$r_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)
-30	0.014 @ $V_{GS} = -10$ V	-11
	0.023 @ $V_{GS} = -4.5$ V	-8.5

### FEATURES

- TrenchFET® Power MOSFET



Pb-free  
Available



P-Channel MOSFET

Ordering Information: Si4425DY  
 Si4425DY-T1 (with Tape and Reel)  
 Si4425DY—E3 (Lead (Pb)-Free)  
 Si4425DY-T1—E3 (Lead (Pb)-Free with Tape and Reel)

ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)					
Parameter	Symbol	10 secs	Steady State	Unit	
Drain-Source Voltage	$V_{DS}$	-30		V	
Gate-Source Voltage	$V_{GS}$	$\pm 20$			
Continuous Drain Current ( $T_J = 150^\circ\text{C}$ ) <sup>a</sup>	$I_D$	$T_A = 25^\circ\text{C}$	-11	-8	A
		$T_A = 70^\circ\text{C}$	-8.7	-6.5	
Pulsed Drain Current	$I_{DM}$	-50			
continuous Source Current (Diode Conduction) <sup>a</sup>	$I_S$	-2.7	-1.36		
Maximum Power Dissipation <sup>a</sup>	$P_D$	$T_A = 25^\circ\text{C}$	3.0	1.5	W
		$T_A = 70^\circ\text{C}$	1.9	0.95	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to 150		$^\circ\text{C}$	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient <sup>a</sup>	$R_{thJA}$	$t \leq 10$ sec	33	42	$^\circ\text{C}/\text{W}$
		Steady State	70	84	
Maximum Junction-to-Foot (Drain)	$R_{thJF}$	16	21		

Notes

a. Surface Mounted on 1" x 1" FR4 Board.

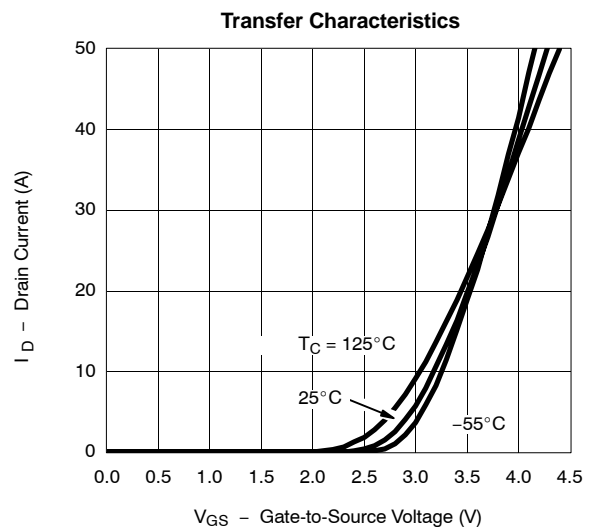
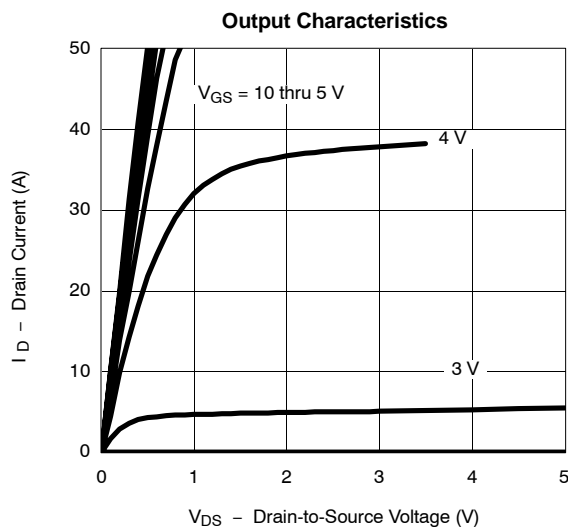
**SPECIFICATIONS (T<sub>J</sub> = 25 °C UNLESS OTHERWISE NOTED)**

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>Static</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250 μA	-1.0	-1.9	-3.0	V
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = -30 V, V <sub>GS</sub> = 0 V			-1	μA
		V <sub>DS</sub> = -30 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 70 °C			-10	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = -5 V, V <sub>GS</sub> = -10 V	-30			A
Drain-Source On-State Resistance <sup>a</sup>	r <sub>DS(on)</sub>	V <sub>GS</sub> = -10 V, I <sub>D</sub> = -11 A		0.010	0.014	Ω
		V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = 8.5 A		0.017	0.023	
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = -15 V, I <sub>D</sub> = -11 A		23		S
Diode Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>S</sub> = -2.7 A, V <sub>GS</sub> = 0 V		-0.75	-1.1	V
<b>Dynamic<sup>b</sup></b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = -15 V, V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -11 A		33	50	nC
Gate-Source Charge	Q <sub>gs</sub>			10		
Gate-Drain Charge	Q <sub>gd</sub>			13		
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = -15 V, R <sub>L</sub> = 10 Ω I <sub>D</sub> ≅ -1 A, V <sub>GEN</sub> = -10 V, R <sub>g</sub> = 6 Ω		20	30	ns
Rise Time	t <sub>r</sub>			15	25	
Turn-Off Delay Time	t <sub>d(off)</sub>			95	150	
Fall Time	t <sub>f</sub>			44	65	
Gate Resistance	R <sub>g</sub>			3.2		Ω
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = -2.1 A, di/dt = 100 A/μs		50	80	ns

## Notes

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.  
b. Guaranteed by design, not subject to production testing.

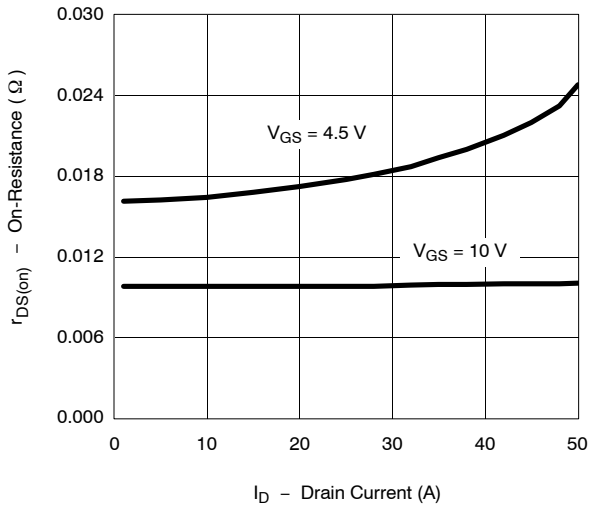
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)**

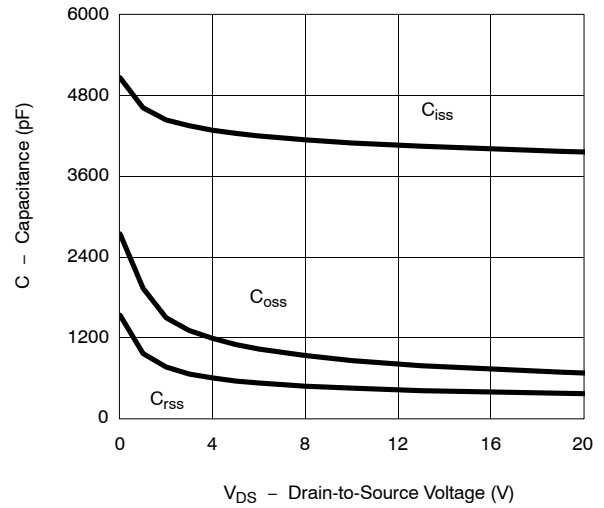


**TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)**

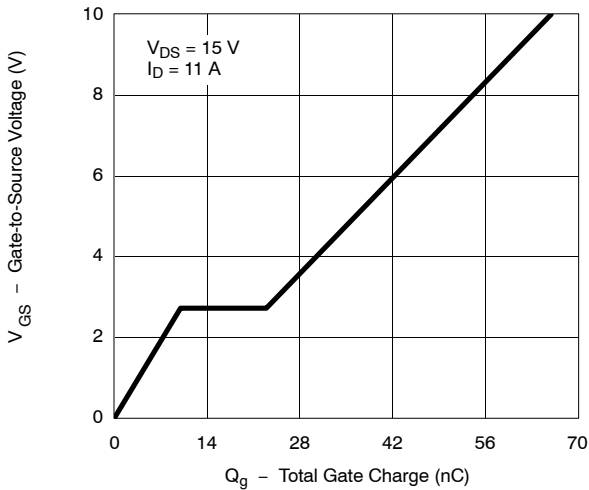
**On-Resistance vs. Drain Current**



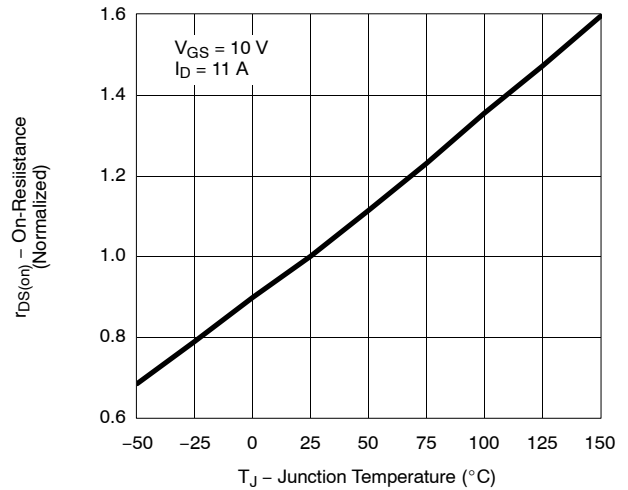
**Capacitance**



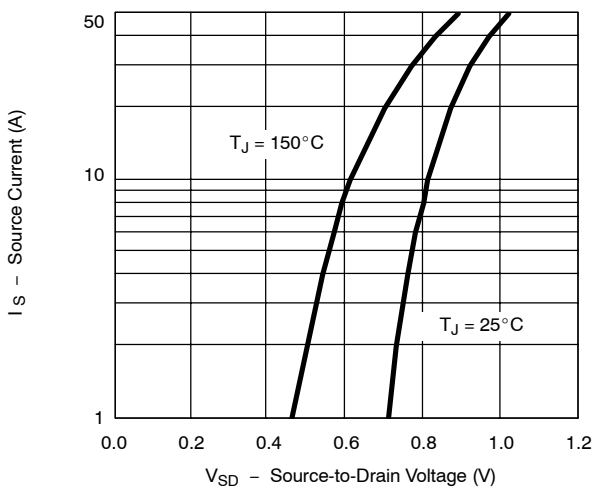
**Gate Charge**



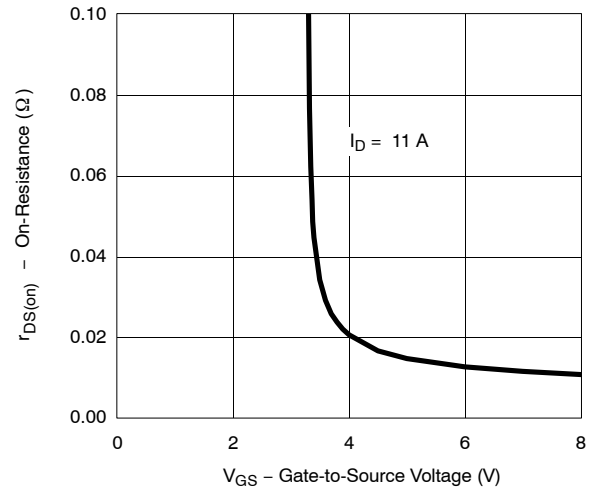
**On-Resistance vs. Junction Temperature**



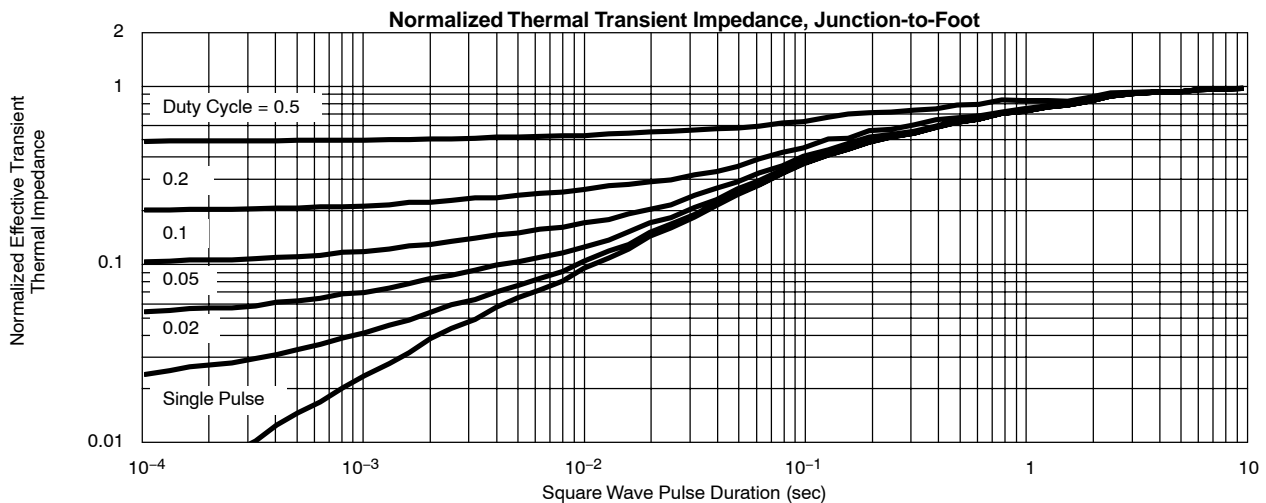
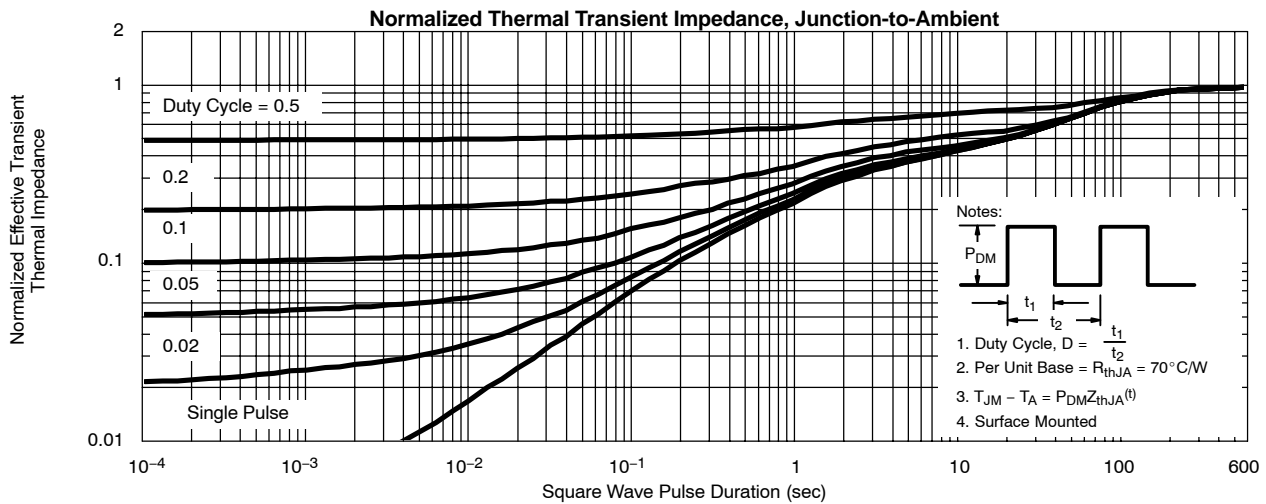
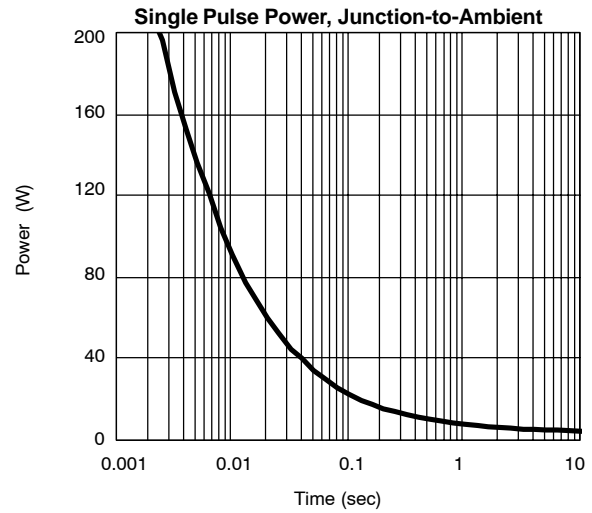
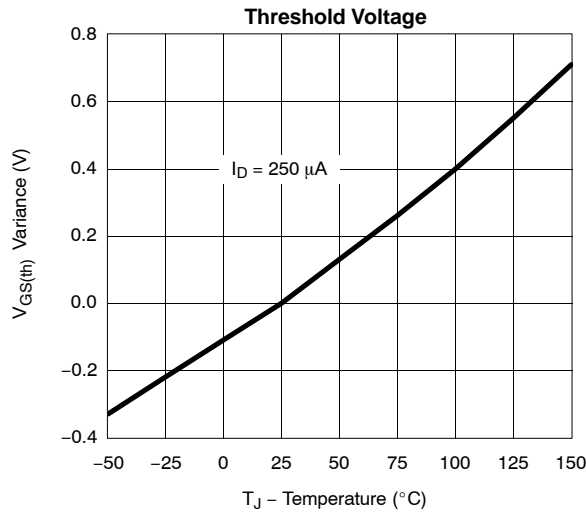
**Source-Drain Diode Forward Voltage**



**On-Resistance vs. Gate-to-Source Voltage**



**TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)**



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